



List of Leading EUVL Technical Challenges

**2015 International Workshop on EUVL
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Source

Power scaling of Sn LPP sources to 250 W

Feasibility of FEL based EUV sources for > 250 to 1000 W

HVM EUV source performance – status and challenges

High brightness EUV sources to support mask metrology

Source power requirements for high NA scanners

Optics and Contamination

High NA optics design including “Anamorphic Optics” design

Innovative collector optics designs for HVM sources

New capping layers for extending lifetime

In-situ optics cleaning

Contamination measurement in EUV tools

Mask

Mask technology to support high NA scanners (design and materials)

Strategies for low defect mask blanks

Mask defect metrology (Actinic and non-actinic inspection)

Mask defect reduction (In-situ mask cleaning and pellicles, defect reduction strategies)

Mask infrastructure readiness

Resist and Patterning

New EUV resists chemistries including high absorption resists

EUV resist outgassing and testing

Negative tone resists and patterning

Role of secondary electrons in EUV resists

Multiple patterning using EUVL

DSA's role in EUVL patterning

EUV Extension to < 7 nm resolution

Multiple patterning vs High NA – technical and economic challenges

EUV resolution enhancement techniques